

General Description

The WSP6067A is the highest performance trench N-ch and P-ch MOSFET with extreme high cell density, which provide excellent RDS(on) and gate charge for most of the synchronous buck converter applications.

The WSP6067A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

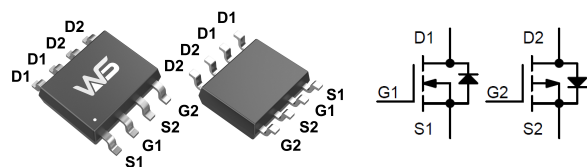
Product Summary

BVDSS	RDS(on)	ID
60V	38mΩ	7A
-60V	80mΩ	-5A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter.
- Networking DC-DC Power System
- Load Switch

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V _{DS}	Drain-Source Voltage	60	-60	V
V _{GS}	Gate-Source Voltage	±20	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	7.0	-5.0	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	4.0	-2.5	A
I _{DM}	Pulsed Drain Current ²	28	-20	A
EAS	Single Pulse Avalanche Energy ³	22	28	mJ
I _{AS}	Avalanche Current	21	-24	A
P _D @T _C =25°C	Total Power Dissipation ⁴	2.0	2.0	W
T _{STG}	Storage Temperature Range	-55 to 150	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	85	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	62.5	°C/W

N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.063	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =5A	---	38	52	mΩ
		V _{GS} =4.5V, I _D =4A	---	55	75	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1	2	3	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.24	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =48V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =4A	---	28	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.8	4.3	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =48V, V _{GS} =4.5V, I _D =4A	---	19	25	nC
Q _{gs}	Gate-Source Charge		---	2.6	---	
Q _{gd}	Gate-Drain Charge		---	4.1	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =3.3Ω, I _D =1A	---	3	---	ns
T _r	Rise Time		---	34	---	
T _{d(off)}	Turn-Off Delay Time		---	23	---	
T _f	Fall Time		---	6	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	1027	---	pF
C _{oss}	Output Capacitance		---	65	---	
C _{rss}	Reverse Transfer Capacitance		---	45	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V, L=0.1mH, I _{AS} =22A	12	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	2.5	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	24	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.3	V

Note :

- The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, t<10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=22A
- The power dissipation is limited by 150°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-60	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.03	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-3A	---	80	100	mΩ
		V _{GS} =-4.5V, I _D =-2A	---	100	115	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.75	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	4.56	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =-48V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	8.5	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.5	2.7	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-48V, V _{GS} =-10V, I _D =-3A	---	13	---	nC
Q _{gs}	Gate-Source Charge		---	2.2	---	
Q _{gd}	Gate-Drain Charge		---	6.3	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-30V, V _{GS} =-10V, R _G =3.3Ω, I _D =-1A	---	9.2	---	ns
T _r	Rise Time		---	20.1	---	
T _{d(off)}	Turn-Off Delay Time		---	46.7	---	
T _f	Fall Time		---	9.4	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	1137	---	pF
C _{oss}	Output Capacitance		---	76	---	
C _{rss}	Reverse Transfer Capacitance		---	50	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =-25V, L=0.1mH, I _{AS} =-24A	13	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	-2.5	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	-10	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH,I_{AS}=-24A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

N-Channel Typical Characteristics

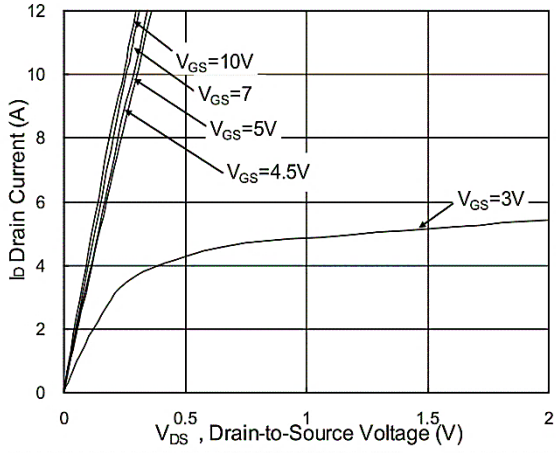


Fig.1 Typical Output Characteristics

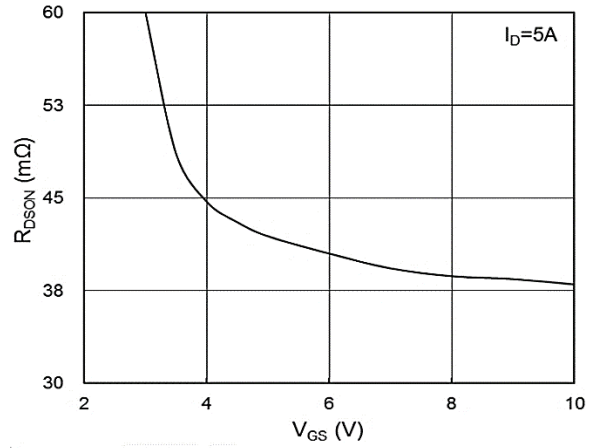


Fig.2 On-Resistance vs. G-S Voltage

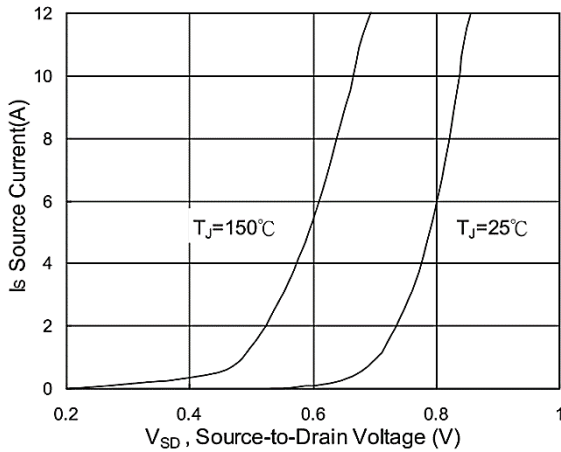


Fig.3 Source Drain Forward Characteristics

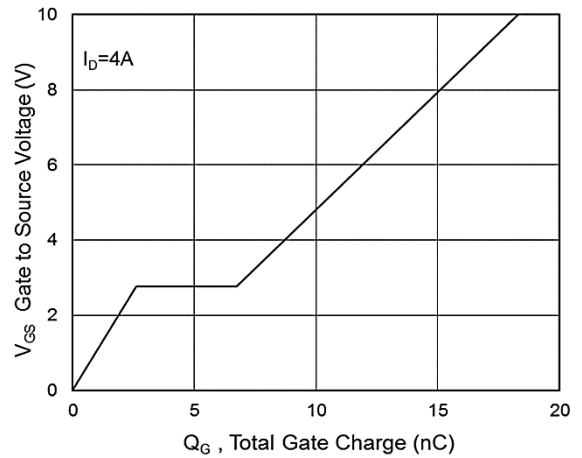


Fig.4 Gate-Charge Characteristics

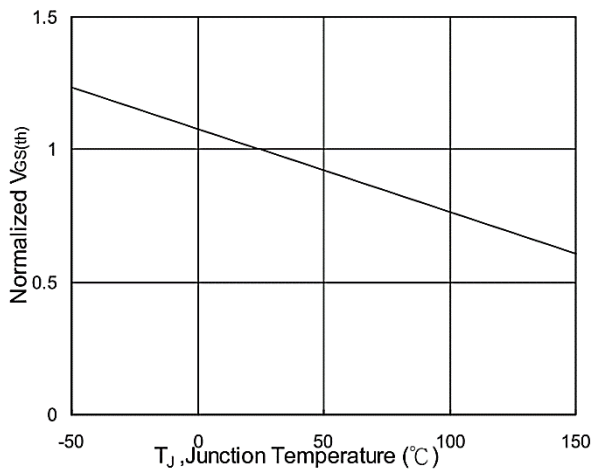


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

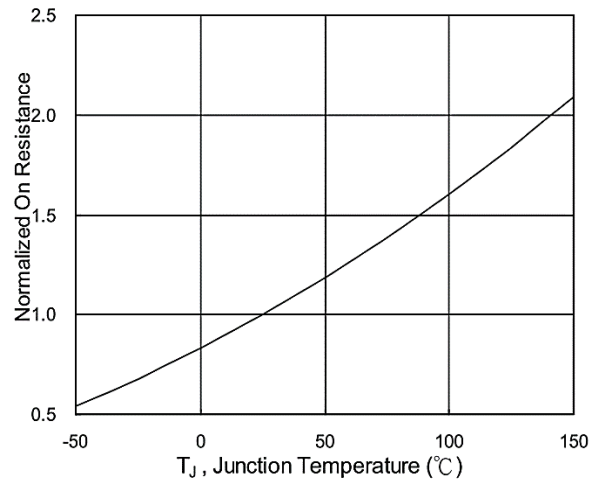


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

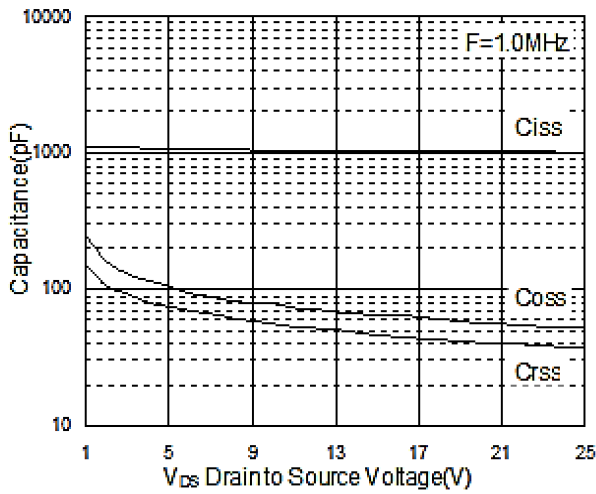


Fig.7 Capacitance

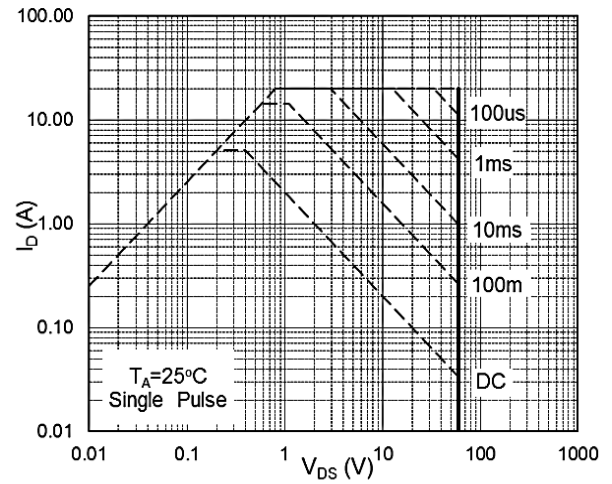


Fig.8 Safe Operating Area

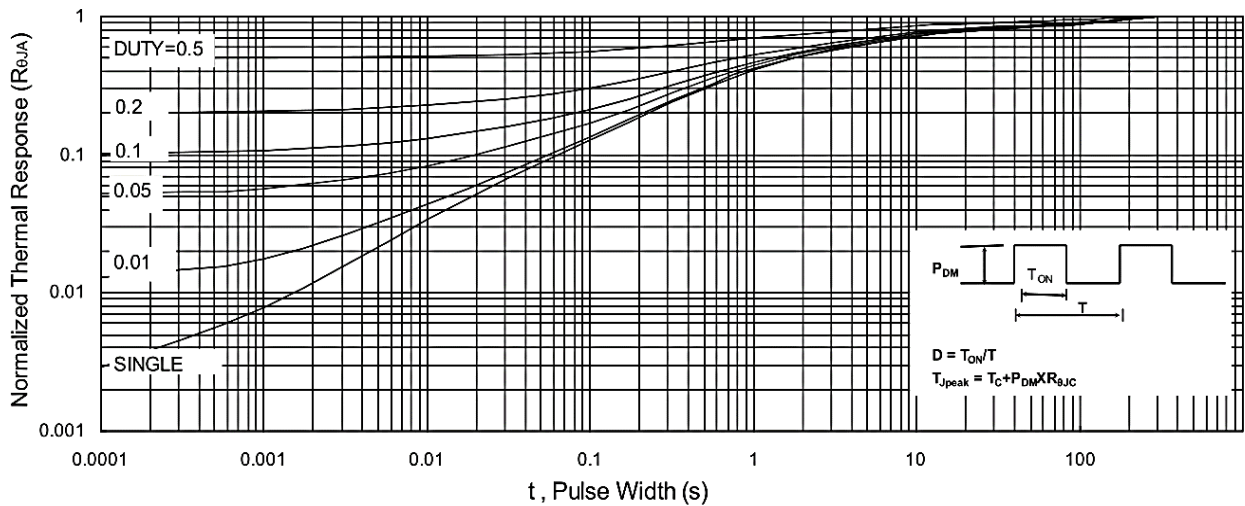


Fig.9 Normalized Maximum Transient Thermal Impedance

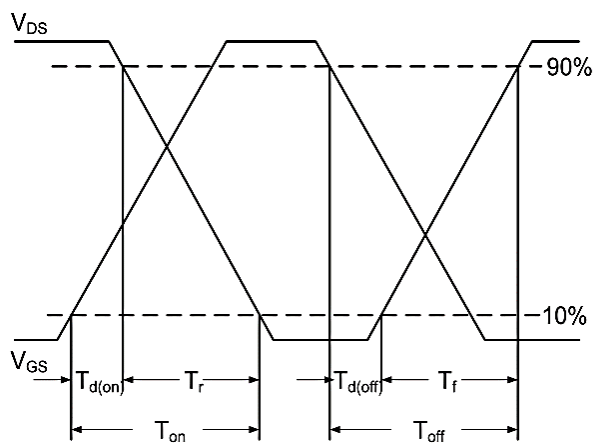


Fig.10 Switching Time Waveform

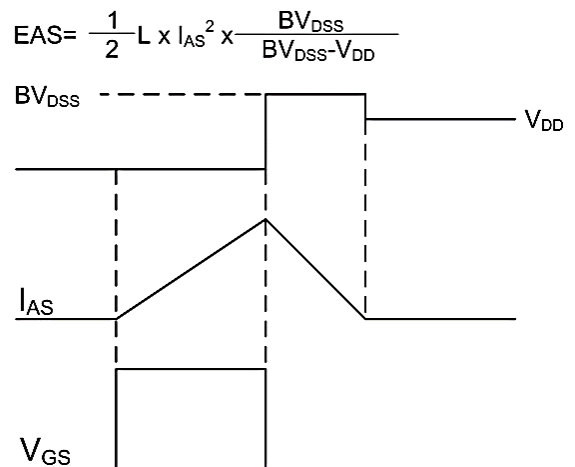


Fig.11 Unclamped Inductive Waveform

P-Channel Typical Characteristics

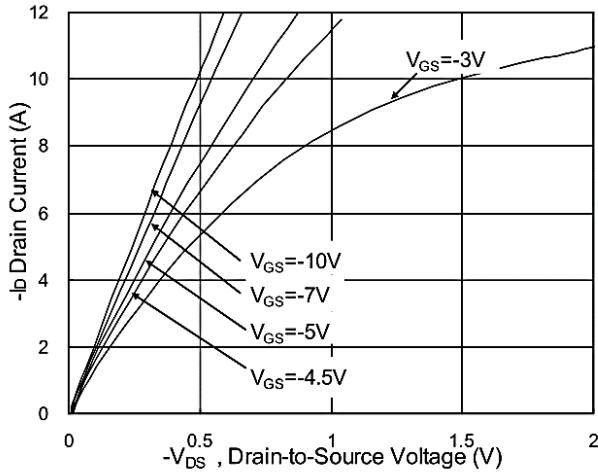


Fig.1 Typical Output Characteristics

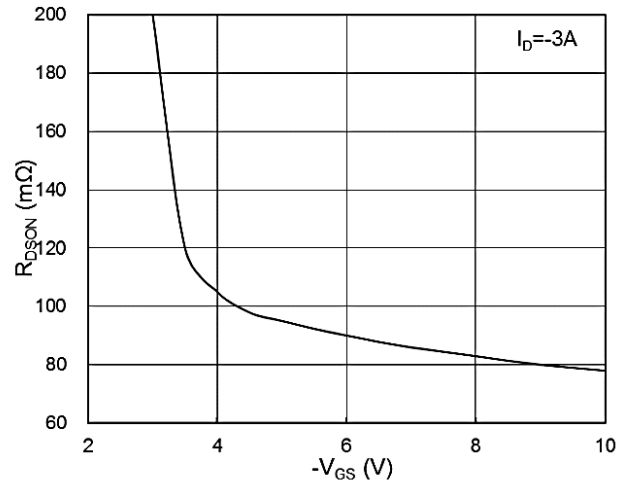


Fig.2 On-Resistance vs. G-S Voltage

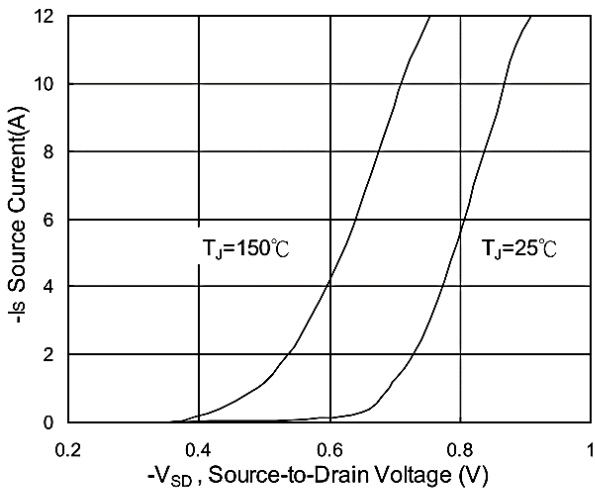


Fig.3 Source Drain Forward Characteristics

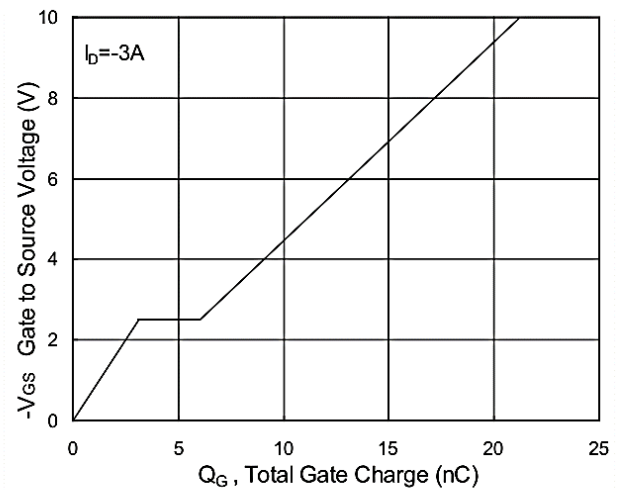


Fig.4 Gate-Charge Characteristics

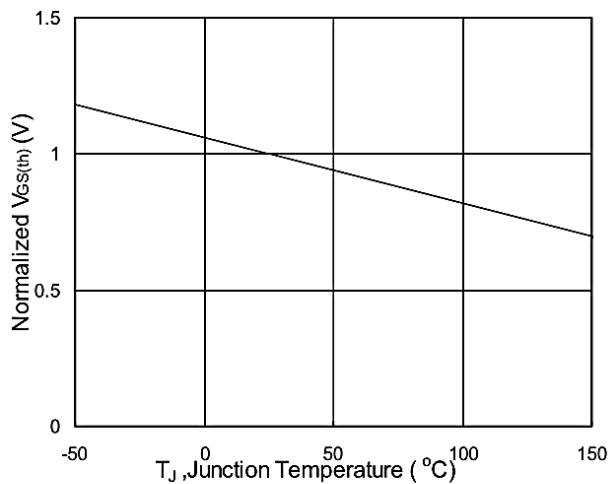


Fig.5 Normalized $V_{GS(th)}$ vs. T_j

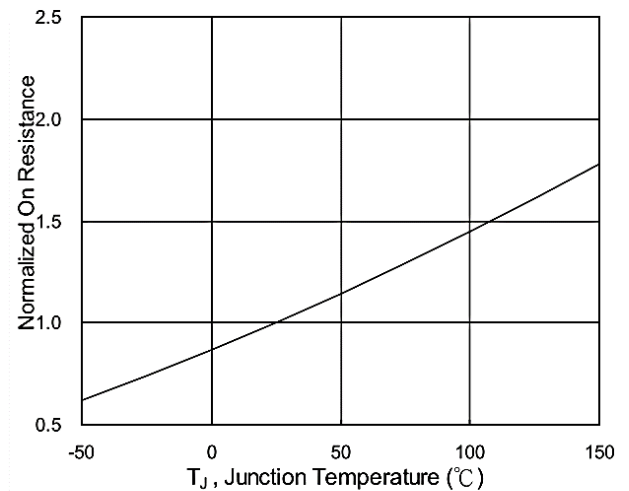


Fig.6 Normalized $R_{DS(on)}$ vs. T_j

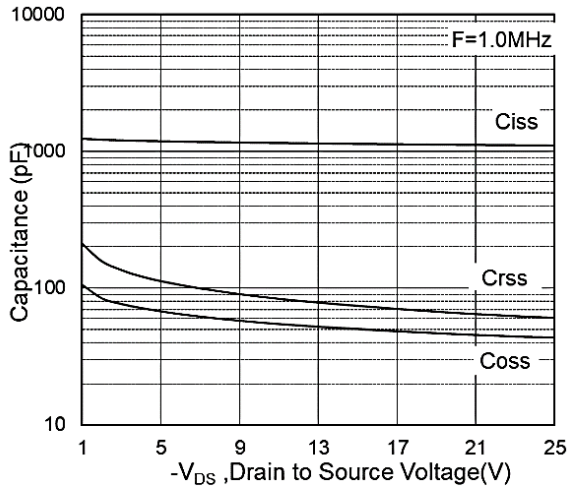


Fig.7 Capacitance

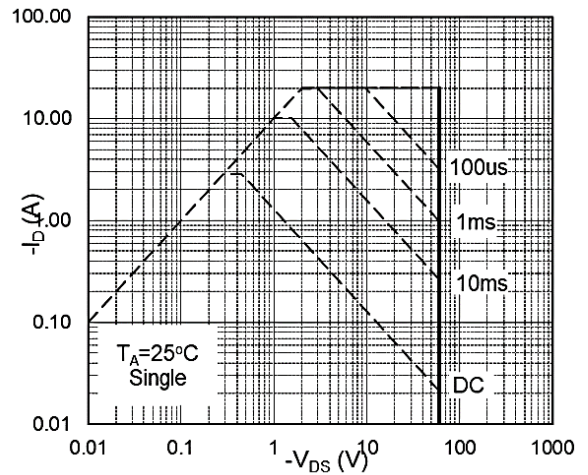


Fig.8 Safe Operating Area

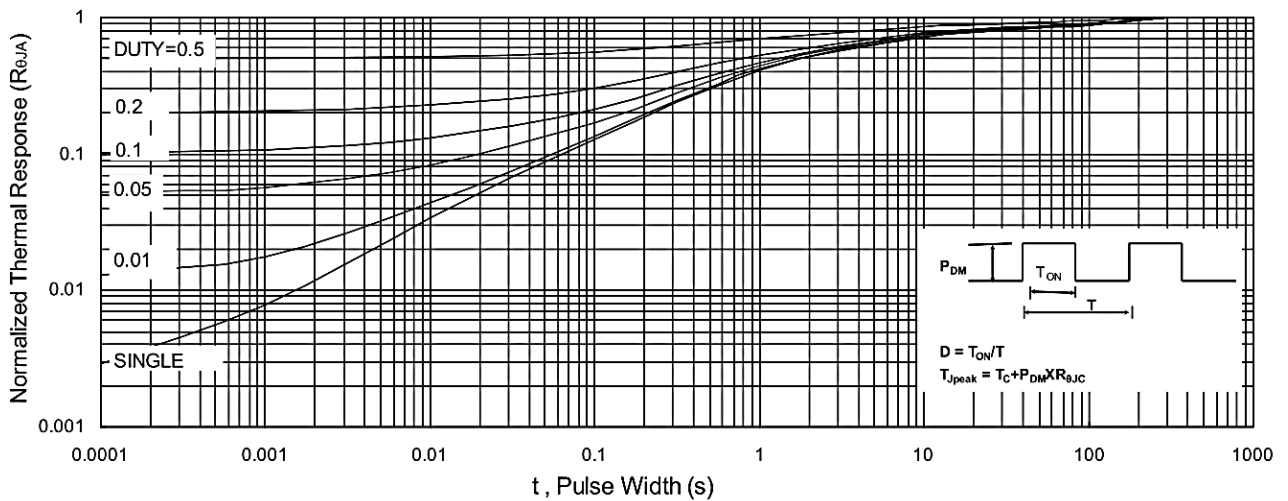


Fig.9 Normalized Maximum Transient Thermal Impedance

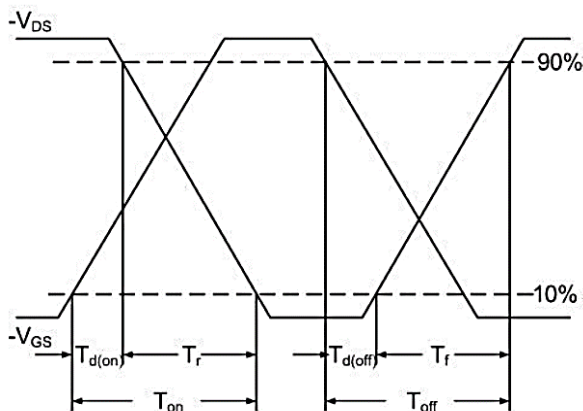


Fig.10 Switching Time Waveform

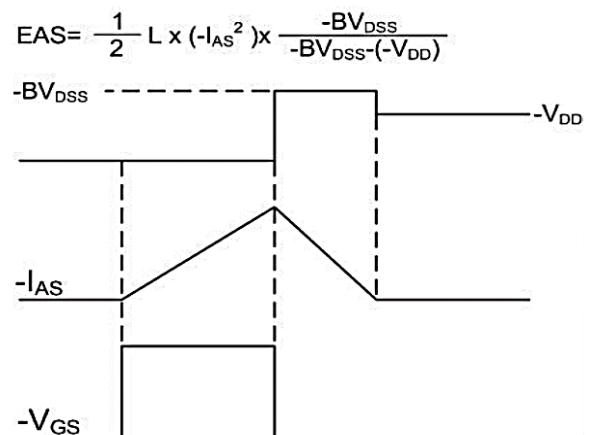


Fig.11 Unclamped Inductive Waveform



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